

SK10DGDL12T7ETE1s



SEMITOP®E1 Solder

3-phase Converter-Inverter-Brake (CIB)

SK10DGDL12T7ETE1s

Features*

- Optimized design for superior thermal performance
- Low inductive design
- Solder contact technology
- 1200V Generation 7 IGBT (T7)
- Robust and soft switching CAL4F diode technology
- PEP rectifier diode technology for enhanced power and environmental robustness
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

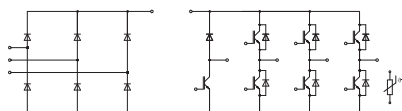
Typical Applications

- Motor drives
- Air conditioning
- Auxiliary Inverters

Remarks

- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	19	A
	T _j = 175 °C	T _s = 100 °C	15	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	20	A
	T _j = 175 °C	T _s = 100 °C	17	A
I _{Cnom}			10	A
I _{CRM}			20	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 175 °C	7	µs
T _j			-40 ... 175	°C
Chopper - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	19	A
	T _j = 175 °C	T _s = 100 °C	15	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	20	A
	T _j = 175 °C	T _s = 100 °C	17	A
I _{Cnom}			10	A
I _{CRM}			20	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 175 °C	7	µs
T _j			-40 ... 175	°C
Inverse - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	12	A
	T _j = 175 °C	T _s = 100 °C	10	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	13	A
	T _j = 175 °C	T _s = 100 °C	11	A
I _{FRM}			20	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		36	A
T _j			-40 ... 175	°C
Freewheeling - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	12	A
	T _j = 175 °C	T _s = 100 °C	10	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	13	A
	T _j = 175 °C	T _s = 100 °C	11	A
I _{FRM}			20	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		36	A
T _j			-40 ... 175	°C



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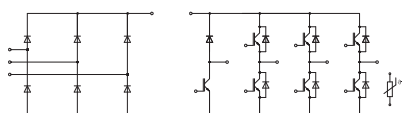
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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Rectifier - Diode				
V _{RRM}	T _j = 25 °C		1600	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	36	A
	T _j = 175 °C	T _s = 100 °C	29	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	40	A
	T _j = 175 °C	T _s = 100 °C	32	A
I _{FSM}	t _p = 10 ms	T _j = 25 °C	220	A
	sin 180°	T _j = 150 °C	200	A
i ² t	t _p = 10 ms	T _j = 25 °C	242	A ² s
	sin 180°	T _j = 150 °C	200	A ² s
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}	, ΔT _{terminal} at PCB joint = 30 K, per pin		30	A
T _{stg}	module without TIM		-40 ... 125	°C
V _{isol}	AC, sinusoidal, 1 min		2500	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
V _{CE(sat)}	I _C = 10 A	T _j = 25 °C		1.60	1.75	V
	V _{GE} = 15 V	T _j = 150 °C		1.78	1.93	V
	chiplevel	T _j = 175 °C		1.82	1.97	V
V _{CE0}		T _j = 25 °C		1.00	1.05	V
	chiplevel	T _j = 150 °C		0.80	0.85	V
		T _j = 175 °C		0.75	0.80	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		60	70	mΩ
	chiplevel	T _j = 150 °C		98	108	mΩ
		T _j = 175 °C		107	117	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0.22 mA		5.15	5.8	6.45	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V, T _j = 25 °C				1	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		1.90		nF
C _{oes}		f = 1 MHz		0.02		nF
C _{res}		f = 1 MHz		0.01		nF
Q _G	V _{GE} = -15 V ... +15 V			140		nC
R _{Gint}	T _j = 25 °C			0		Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 25 °C		13		ns
	I _C = 10 A	T _j = 150 °C		16		ns
	R _{G on} = 8.2 Ω	T _j = 175 °C		17		ns
t _r	R _{G off} = 8.2 Ω	T _j = 25 °C		18		ns
	V _{GE} = +15/-15 V	T _j = 150 °C		19		ns
	(T _j = 150 °C)	T _j = 175 °C		20		ns
E _{on}	di/dt _{on} = 700 A/μs	T _j = 25 °C		0.42		mJ
	di/dt _{off} = 120 A/μs	T _j = 150 °C		0.74		mJ
	dv/dt = 3700 V/μs	T _j = 175 °C		0.81		mJ



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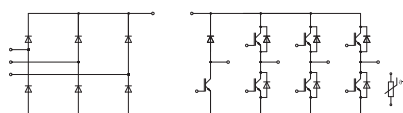
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- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)



DGDL-ET

Characteristics					
Symbol	Conditions		min.	typ.	max. Unit
Inverter - IGBT					
$t_{d(off)}$	$V_{CC} = 600 \text{ V}$	$T_j = 25 \text{ }^{\circ}\text{C}$		199	ns
	$I_C = 10 \text{ A}$	$T_j = 150 \text{ }^{\circ}\text{C}$		270	ns
	$R_{G on} = 8.2 \text{ } \Omega$	$T_j = 175 \text{ }^{\circ}\text{C}$		293	ns
t_f	$R_{G off} = 8.2 \text{ } \Omega$	$T_j = 25 \text{ }^{\circ}\text{C}$		52	ns
	$V_{GE} = +15/-15 \text{ V}$	$T_j = 150 \text{ }^{\circ}\text{C}$		69	ns
		$T_j = 175 \text{ }^{\circ}\text{C}$		95	ns
E_{off}	$(T_j = 150 \text{ }^{\circ}\text{C})$	$T_j = 25 \text{ }^{\circ}\text{C}$		0.75	mJ
	$di/dt_{on} = 700 \text{ A}/\mu\text{s}$	$T_j = 150 \text{ }^{\circ}\text{C}$		1.26	mJ
	$di/dt_{off} = 120 \text{ A}/\mu\text{s}$	$T_j = 175 \text{ }^{\circ}\text{C}$		1.37	mJ
	$dv/dt = 3700 \text{ V}/\mu\text{s}$				
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8 \text{ W}/(\text{mK})$			1.91	K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5 \text{ W}/(\text{mK})$			1.56	K/W
Chopper - IGBT					
$V_{CE(sat)}$	$I_C = 10 \text{ A}$	$T_j = 25 \text{ }^{\circ}\text{C}$		1.60	1.75 V
	$V_{GE} = 15 \text{ V}$	$T_j = 150 \text{ }^{\circ}\text{C}$		1.78	1.93 V
	chiplevel	$T_j = 175 \text{ }^{\circ}\text{C}$		1.82	1.97 V
V_{CE0}		$T_j = 25 \text{ }^{\circ}\text{C}$		1.00	1.05 V
	chiplevel	$T_j = 150 \text{ }^{\circ}\text{C}$		0.80	0.85 V
		$T_j = 175 \text{ }^{\circ}\text{C}$		0.75	0.80 V
r_{CE}	$V_{GE} = 15 \text{ V}$	$T_j = 25 \text{ }^{\circ}\text{C}$		60	70 m Ω
	chiplevel	$T_j = 150 \text{ }^{\circ}\text{C}$		98	108 m Ω
		$T_j = 175 \text{ }^{\circ}\text{C}$		107	117 m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 0.22 \text{ mA}$		5.15	5.8	6.45 V
I_{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = 1200 \text{ V}, T_j = 25 \text{ }^{\circ}\text{C}$				1 mA
C_{ies}		$f = 1 \text{ MHz}$		1.90	nF
C_{oes}	$V_{CE} = 25 \text{ V}$	$f = 1 \text{ MHz}$		0.02	nF
C_{res}	$V_{GE} = 0 \text{ V}$	$f = 1 \text{ MHz}$		0.01	nF
Q_G	$V_{GE} = -15 \text{ V} \dots +15 \text{ V}$			140	nC
R_{Gint}	$T_j = 25 \text{ }^{\circ}\text{C}$			0	Ω
$t_{d(on)}$		$T_j = 25 \text{ }^{\circ}\text{C}$		13	ns
		$T_j = 150 \text{ }^{\circ}\text{C}$		16	ns
		$T_j = 175 \text{ }^{\circ}\text{C}$		17	ns
t_r		$T_j = 25 \text{ }^{\circ}\text{C}$		18	ns
		$T_j = 150 \text{ }^{\circ}\text{C}$		19	ns
		$T_j = 175 \text{ }^{\circ}\text{C}$		20	ns
E_{on}	$V_{CC} = 600 \text{ V}$	$T_j = 25 \text{ }^{\circ}\text{C}$		0.42	mJ
	$I_C = 10 \text{ A}$	$T_j = 150 \text{ }^{\circ}\text{C}$		0.74	mJ
	$R_{G on} = 8.2 \text{ } \Omega$	$T_j = 175 \text{ }^{\circ}\text{C}$		0.81	mJ
	$R_{G off} = 8.2 \text{ } \Omega$				
	$V_{GE} = +15/-15 \text{ V}$				
$t_{d(off)}$		$T_j = 25 \text{ }^{\circ}\text{C}$		199	ns
	$(T_j = 150 \text{ }^{\circ}\text{C})$	$T_j = 150 \text{ }^{\circ}\text{C}$		270	ns
	$di/dt_{on} = 700 \text{ A}/\mu\text{s}$	$T_j = 175 \text{ }^{\circ}\text{C}$		293	ns
t_f	$di/dt_{off} = 120 \text{ A}/\mu\text{s}$	$T_j = 25 \text{ }^{\circ}\text{C}$		52	ns
	$dv/dt = 3700 \text{ V}/\mu\text{s}$	$T_j = 150 \text{ }^{\circ}\text{C}$		69	ns
		$T_j = 175 \text{ }^{\circ}\text{C}$		95	ns
E_{off}		$T_j = 25 \text{ }^{\circ}\text{C}$		0.75	mJ
		$T_j = 150 \text{ }^{\circ}\text{C}$		1.26	mJ
		$T_j = 175 \text{ }^{\circ}\text{C}$		1.37	mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8 \text{ W}/(\text{mK})$			1.91	K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5 \text{ W}/(\text{mK})$			1.56	K/W

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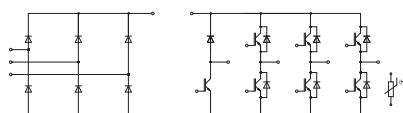
Typical Applications

- Motor drives
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Remarks

- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)

Characteristics					
Symbol	Conditions		min.	typ.	max. Unit
Inverse - Diode					
$V_F = V_{EC}$	$I_F = 10 \text{ A}$	$T_j = 25 \text{ }^{\circ}\text{C}$		2.59	2.94 V
		$T_j = 150 \text{ }^{\circ}\text{C}$		2.71	3.08 V
	chiplevel	$T_j = 175 \text{ }^{\circ}\text{C}$		2.53	2.89 V
V_{F0}		$T_j = 25 \text{ }^{\circ}\text{C}$		1.30	1.50 V
	chiplevel	$T_j = 150 \text{ }^{\circ}\text{C}$		0.90	1.10 V
		$T_j = 175 \text{ }^{\circ}\text{C}$		0.82	0.98 V
r_F		$T_j = 25 \text{ }^{\circ}\text{C}$		129	144 mΩ
	chiplevel	$T_j = 150 \text{ }^{\circ}\text{C}$		181	198 mΩ
		$T_j = 175 \text{ }^{\circ}\text{C}$		171	191 mΩ
I_{RRM}		$T_j = 25 \text{ }^{\circ}\text{C}$		8	A
		$T_j = 150 \text{ }^{\circ}\text{C}$		14	A
		$T_j = 175 \text{ }^{\circ}\text{C}$		16	A
Q_{rr}	$V_{CC} = 600 \text{ V}$ $I_F = 10 \text{ A}$	$T_j = 25 \text{ }^{\circ}\text{C}$		0.58	μC
	$V_{GE} = -15 \text{ V}$ ($T_j = 150 \text{ }^{\circ}\text{C}$)	$T_j = 150 \text{ }^{\circ}\text{C}$		2.01	μC
		$T_j = 175 \text{ }^{\circ}\text{C}$		2.37	μC
E_{rr}	$di/dt_{off} = 790 \text{ A/}\mu\text{s}$	$T_j = 25 \text{ }^{\circ}\text{C}$		0.36	mJ
		$T_j = 150 \text{ }^{\circ}\text{C}$		0.91	mJ
		$T_j = 175 \text{ }^{\circ}\text{C}$		1.16	mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8 \text{ W/(mK)}$			2.64	K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 2.5 \text{ W/(mK)}$			2.24	K/W
Freewheeling - Diode					
$V_F = V_{EC}$	$I_F = 10 \text{ A}$	$T_j = 25 \text{ }^{\circ}\text{C}$		2.59	2.94 V
		$T_j = 150 \text{ }^{\circ}\text{C}$		2.71	3.08 V
	chiplevel	$T_j = 175 \text{ }^{\circ}\text{C}$		2.53	2.89 V
V_{F0}		$T_j = 25 \text{ }^{\circ}\text{C}$		1.30	1.50 V
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Q_{rr}	$V_{CC} = 600 \text{ V}$ $I_F = 10 \text{ A}$	$T_j = 25 \text{ }^{\circ}\text{C}$		0.58	μC
	$V_{GE} = -15 \text{ V}$ ($T_j = 150 \text{ }^{\circ}\text{C}$)	$T_j = 150 \text{ }^{\circ}\text{C}$		2.01	μC
		$T_j = 175 \text{ }^{\circ}\text{C}$		2.37	μC
E_{rr}	$di/dt_{off} = 790 \text{ A/}\mu\text{s}$	$T_j = 25 \text{ }^{\circ}\text{C}$		0.36	mJ
		$T_j = 150 \text{ }^{\circ}\text{C}$		0.91	mJ
		$T_j = 175 \text{ }^{\circ}\text{C}$		1.16	mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 0.8 \text{ W/(mK)}$			2.64	K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste} = 2.5 \text{ W/(mK)}$			2.24	K/W



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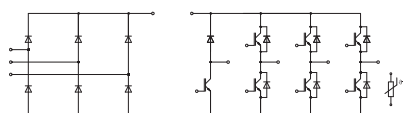
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Rectifier - Diode						
V _F	I _F = 10 A chiplevel	T _j = 25 °C		0.99	1.23	V
		T _j = 150 °C		0.87	1.11	V
		T _j = 175 °C		0.85	1.09	V
V _{F0}	chiplevel	T _j = 25 °C		0.89	1.09	V
		T _j = 150 °C		0.73	0.92	V
		T _j = 175 °C		0.69	0.88	V
r _F	chiplevel	T _j = 25 °C		10	14	mΩ
		T _j = 150 °C		14	19	mΩ
		T _j = 175 °C		16	21	mΩ
I _R	T _j = 150 °C, V _{RRM}			2		mA
R _{th(j-s)}	per Diode, λ _{paste} =0.8 W/(mK)			1.75		K/W
R _{th(j-s)}	per Diode, λ _{paste} =2.5 W/(mK)			1.51		K/W
Module						
M _s	to heatsink		1.6		2.3	Nm
w				25		g
L _{CE}				30		nH
Temperature Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)			493 ± 5%		Ω
B _{25/85}	R _(T) =R ₂₅ *exp[B _{25/85} *(1/T-1/298)], T[K]			3420		K



DGDLE-T

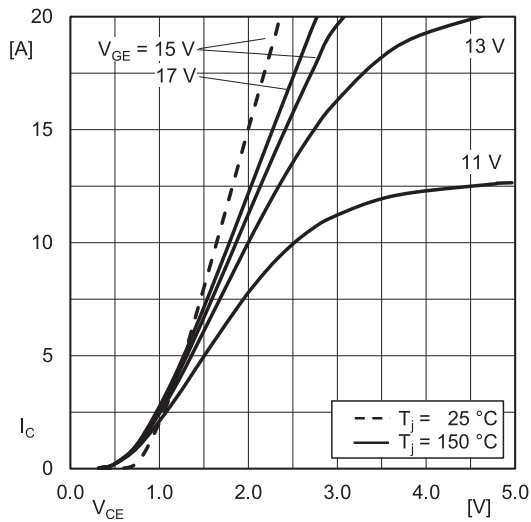


Fig. 1: Typ. IGBT output characteristic, incl. $R_{CC+EE'}$

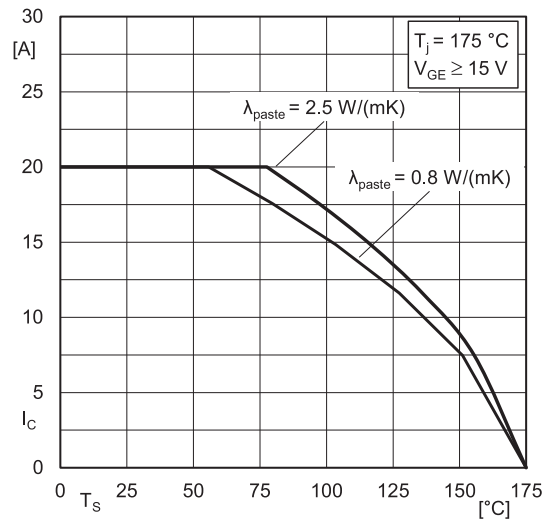


Fig. 2: IGBT rated current vs. temperature $I_C=f(T_s)$

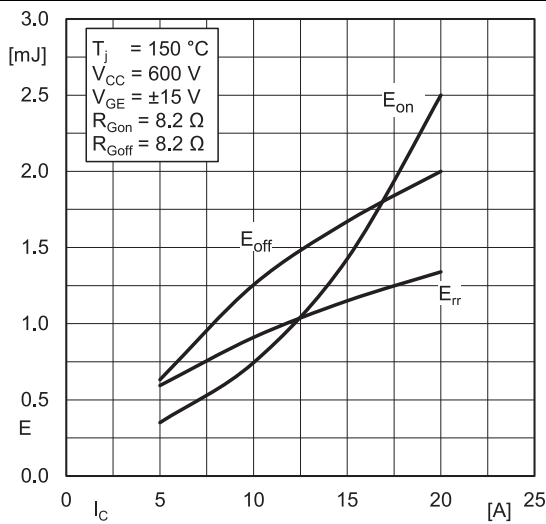


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

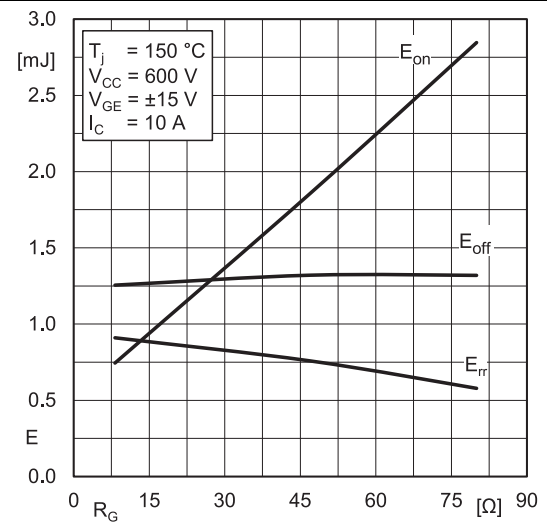


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

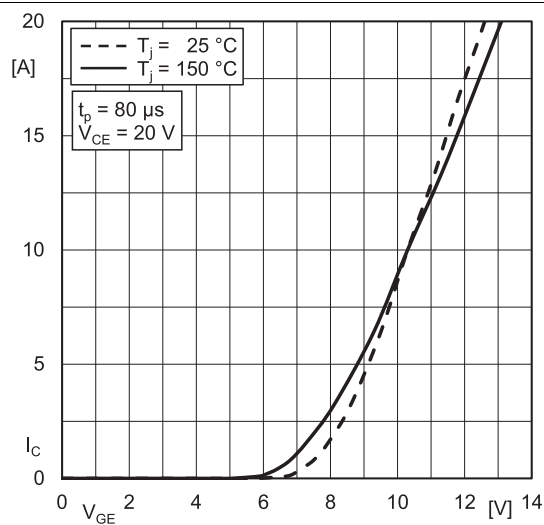


Fig. 5: Typ. IGBT transfer characteristic

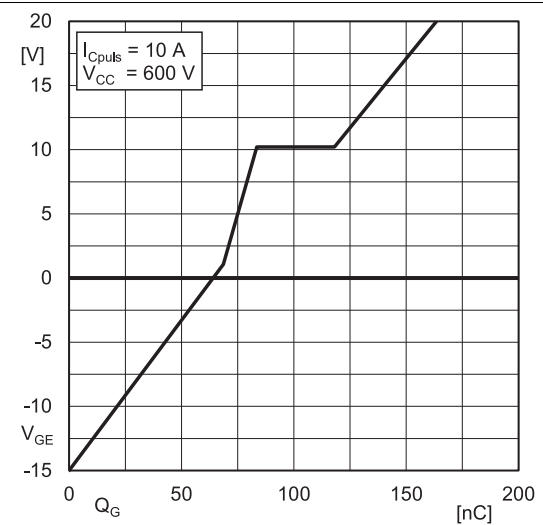


Fig. 6: Typ. IGBT gate charge characteristic

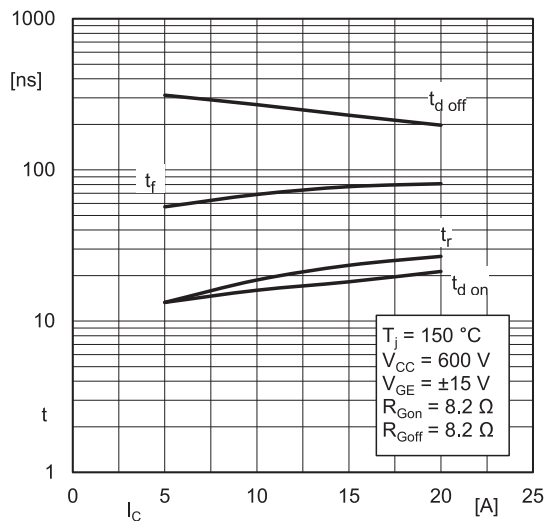


Fig. 7: Typ. switching times = f (I_C)

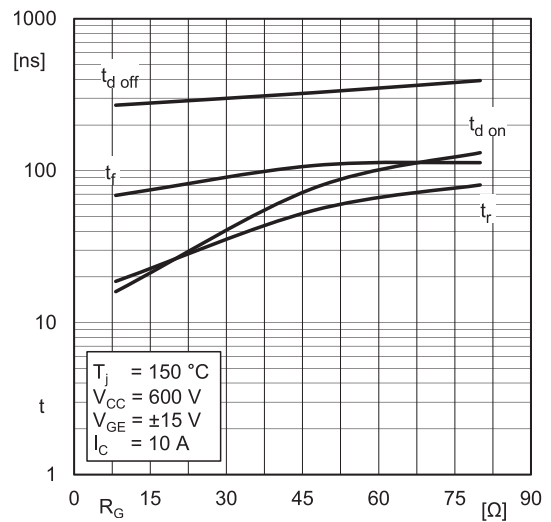


Fig. 8: Typ. switching times = f (R_G)

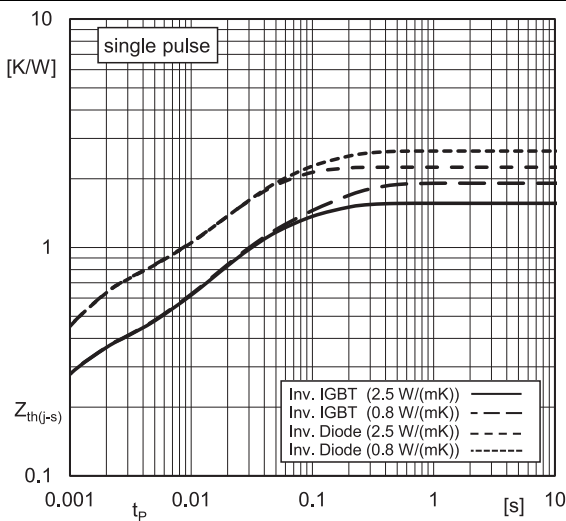


Fig. 9: Typ. transient thermal impedance

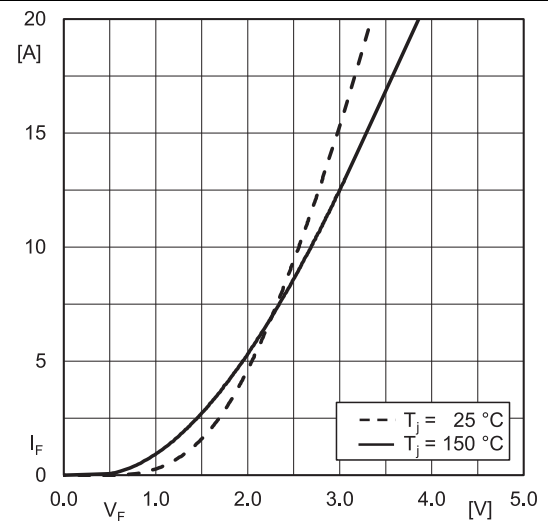


Fig. 10: Typ. Inv. diode forward charact., incl. R_{CC'+EE'}

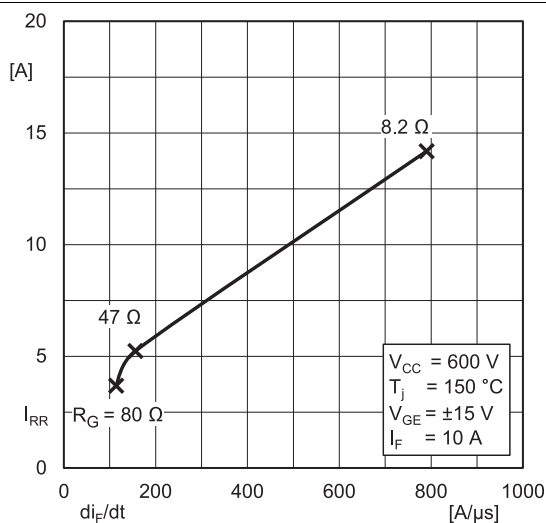


Fig. 11: Typ. Inv. diode peak reverse recovery current

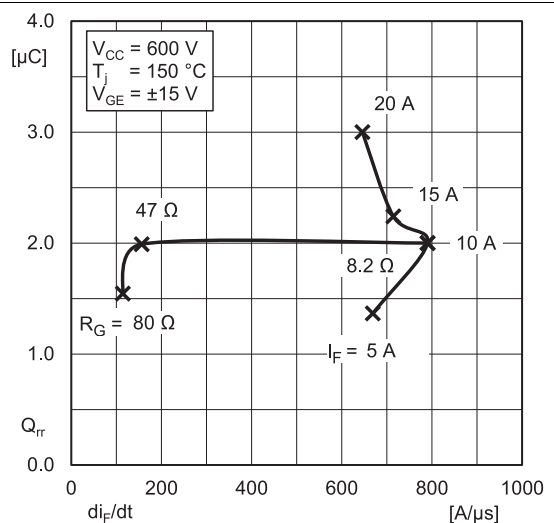


Fig. 12: Typ. Inv. diode reverse recovery charge

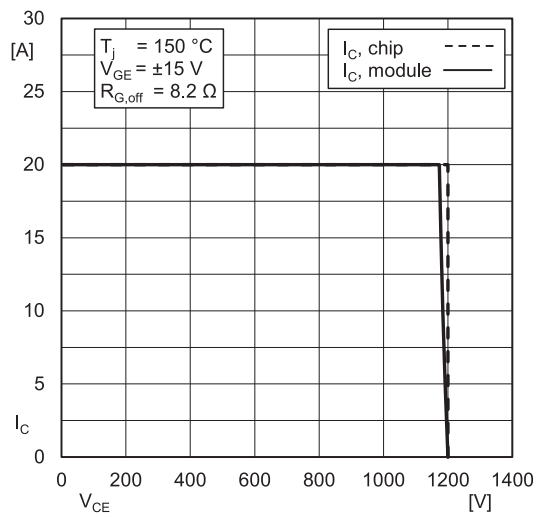


Fig. 13: IGBT Reverse Bias Safe Operating Area (RBSOA)

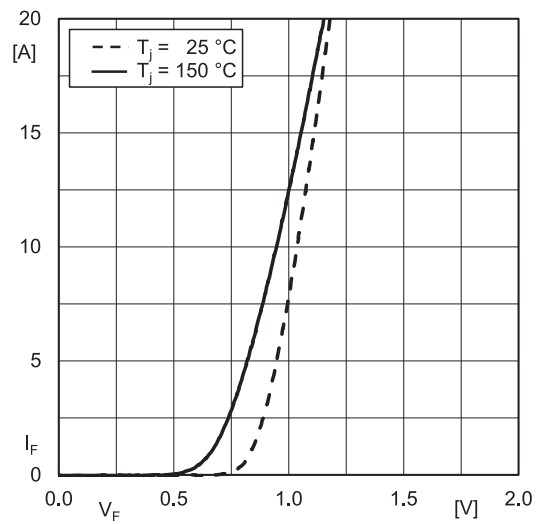
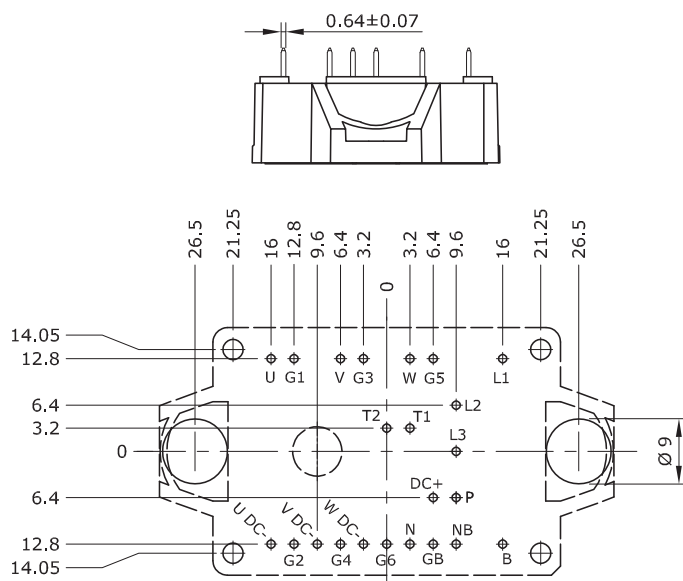
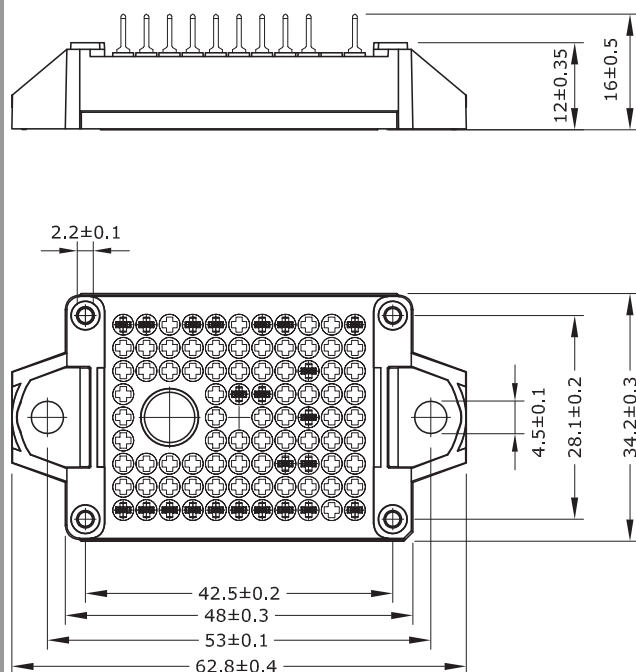


Fig. 14: Typ. Rect. diode forward charact., incl. $R_{CC'+EE'}$

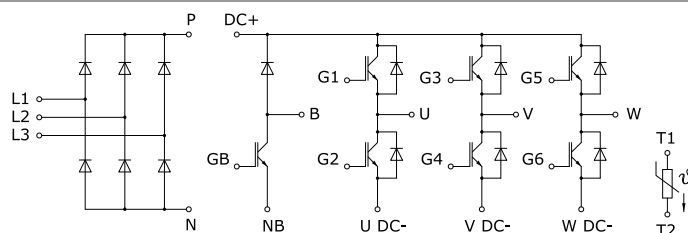
SK10DGDL12T7ETE1s



- Pin-Grid 3.2 mm

- Tolerance of pinpositions ± 0.4

SEMITOP®E1 Solder



DGDL-ET

This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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